



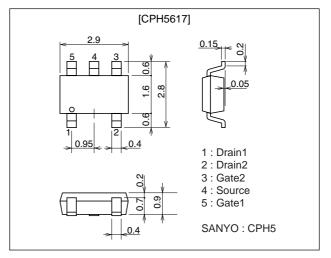
Ultrahigh-Speed Switching Applications

Features

- · Low ON-resistance.
- · Ultrahigh-speed switching.
- 2.5V drive.
- Composite type with 2 MOSFETs contained in the one package, improving the mounting efficiency greatly.

Package Dimensions

unit : mm 2168



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		30	V
Gate-to-Source Voltage	VGSS		±10	V
Drain Current (DC)	ΙD		150	mA
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	600	mA
Allowable Power Dissipation	PD		0.25	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

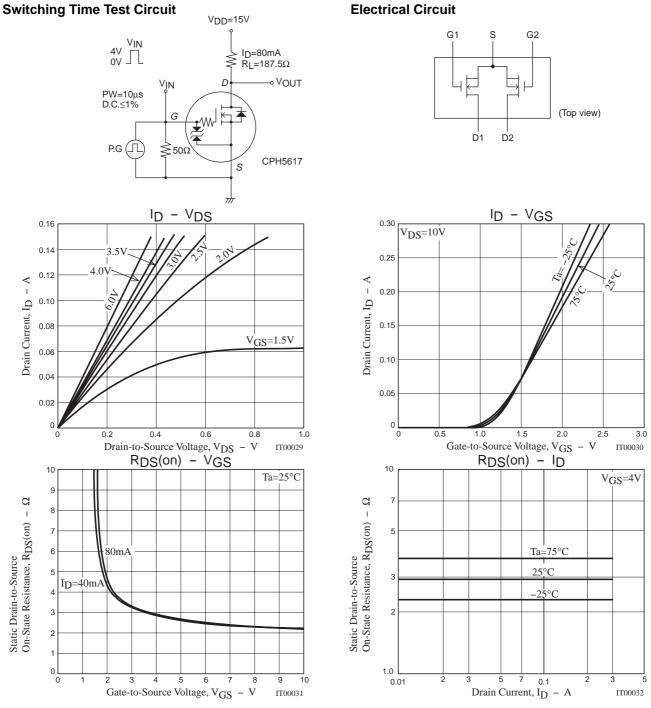
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Oill
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0	30			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =30V, V _{GS} =0			10	μΑ
Gate-to-Sourse Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0			±10	μΑ
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =100μA	0.4		1.3	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =80mA	0.15	0.22		S

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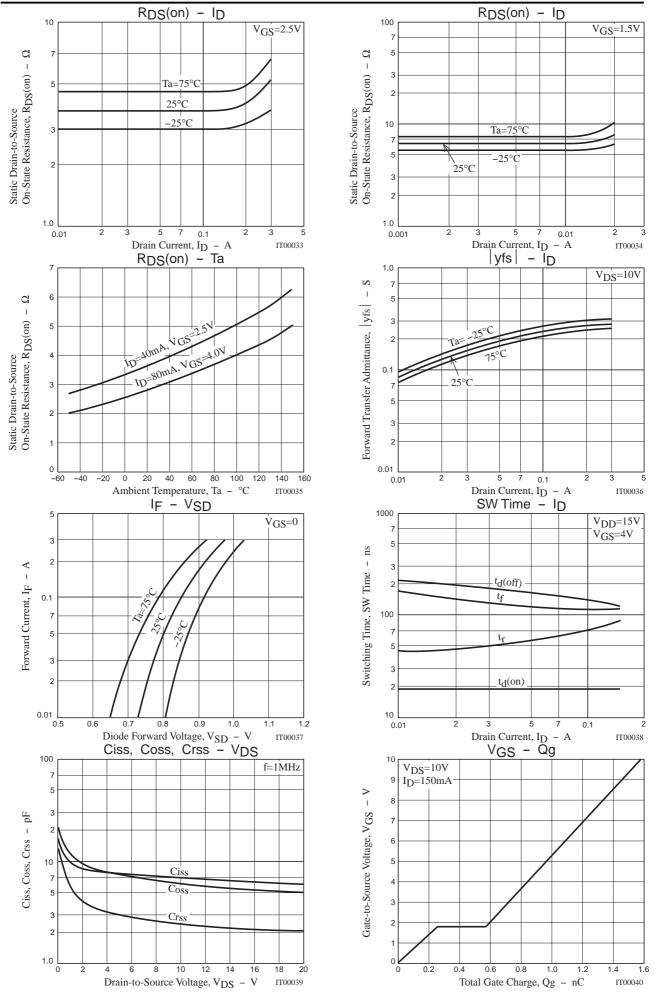
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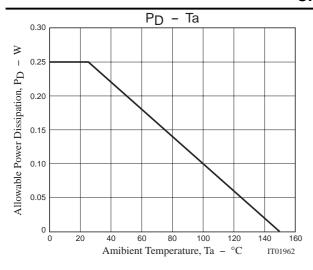
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Static Drain-to-Sourse On-State Resistance	R _{DS} (on)1	I _D =80mA, V _{GS} =4V		2.9	3.7	Ω
	R _{DS} (on)2	I _D =40mA, V _{GS} =2.5V		3.7	5.2	Ω
	RDS(on)3	ID=10mA, VGS=1.5V		6.4	12.8	Ω
Input Capacitance	Ciss	V _{DS} =10V, f=1MHz		7.0		pF
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		5.9		pF
Reverse Transfer Capacitance	Crss	V _{DS} =10V, f=1MHz		2.3		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		19		ns
Rise Time	t _r	See specified Test Circuit.		65		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		155		ns
Fall Time	tf	See specified Test Circuit.		120		ns
Total Gate Charge	Qg	V _{DS} =10V, V _{GS} =10V, I _D =150mA		1.58		nC
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =10V, I _D =150mA		0.26		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =10V, V _{GS} =10V, I _D =150mA		0.31		nC
Diode Forward Voltage	V _{SD}	I _S =150mA, V _{GS} =0		0.87	1.2	V



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